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TECHNICAL SPECIFICATION

Nanomanufacturing - Key control characteristics - Part 6-26: Graphene-related products - Fracture strain and stress, Young's modulus, residual strain and residual stress: bulge test

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Nanomanufacturing - Key control characteristics - Part 6-26: Graphene-related products - Fracture strain and stress, Young's modulus, residual strain and residual stress: bulge test

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Full information on the voting for its approval can be found in the report on voting indicated in the above table.

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